



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
700V	1.3Ω @ $V_{GS} = 10V$	4.6A

Features and Benefits

- Low On-Resistance
- High BV_{DSS} Rating for Power Application
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

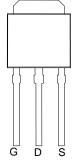
Mechanical Data

- Case: TO251
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)

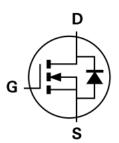


TO251 Top View

TO251 Bottom View



Top View Pin Configuration



Internal Schematic

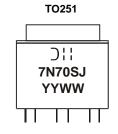
Ordering Information (Note 4)

Part Number	Case	Packaging
DMJ70H1D3SJ3	TO251	75 Pieces/Tube

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information

Notes:



☐ I = Manufacturer's Marking

7N70SJ = Product Type Marking Code

YYWW = Date Code Marking

YY or YY= Last Digit of Year (ex: 16 = 2016)

WW or WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V _{DSS}	700	V	
Gate-Source Voltage	V _{GSS}	±30	V	
Continuous Drain Current (Note 5) $V_{GS} = 10V$ $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$		I _D	4.6 2.9	А
Maximum Body Diode Forward Current (Note 6)	I _S	3.0	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	5.4	А
Avalanche Current (Note 7)	L = 60mH	I _{AS}	1.1	A
Avalanche Energy (Note 7)	L = 60mH	E _{AS}	40	mJ
Peak Diode Recovery dv/dt (Note 7)	•	dv/dt	5	V/ns

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	$T_C = +25$ °C	D-	41	W
Total Fower Dissipation (Note 3)	$T_{C} = +100^{\circ}C$	P _D	16	
Thermal Resistance, Junction to Ambient (Note 6)	R _{ΘJA}	79	°C/W	
Thermal Resistance, Junction to Case (Note 5)	R _{OJC}	3.0	C/VV	
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C	

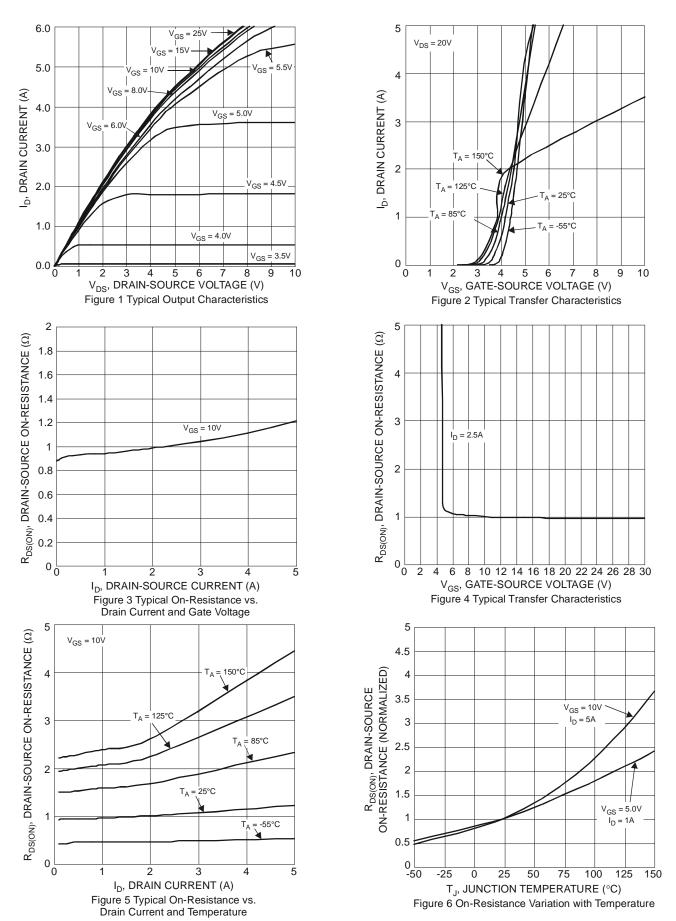
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	700	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	V _{DS} = 700V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	100	nA	$V_{GS} = \pm 30V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)	ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	2	2.9	4	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	1.0	1.3	Ω	$V_{GS} = 10V, I_D = 2.5A$	
Diode Forward Voltage	V _{SD}	_	0.9	1.3	V	$V_{GS} = 0V, I_{S} = 5A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{ISS}	_	351	_		V _{DS} = 50V, f = 1MHz,	
Output Capacitance	Coss		66		pF	$V_{DS} = 50V$, $I = IWIDZ$, $V_{GS} = 0V$	
Reverse Transfer Capacitance	C _{RSS}	_	1.1	_		VGS = 0V	
Gate Resistance	R _G	_	3.5	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q _G	_	13.9	_		V _{DD} = 560V, I _D = 5A, V _{GS} = 10V	
Gate-Source Charge	Q _{GS}	_	1.9	_	nC		
Gate-Drain Charge	Q _{GD}	_	8.5	_			
Turn-On Delay Time	t _{D(ON)}	_	8.5	_		$V_{DD} = 350V$, $V_{GS} = 10V$, $R_G = 4.7\Omega$, $I_D = 2.5A$	
Turn-On Rise Time	t _R	_	11.6	_	20		
Turn-Off Delay Time	t _{D(OFF)}	_	24.5	_	ns		
Turn-Off Fall Time	t _F	_	10	_			
Body Diode Reverse Recovery Time	t _{RR}	_	212		ns		
Body Diode Reverse Recovery Time (T _J = +150°C)	t _{RR}		251		ns		
Body Diode Reverse Recovery Charge	Q_{RR}		1.8		μC	-I _S = 5A, dl/dt = 100A/μs	
Body Diode Reverse Recovery Charge (T _J = +150°C)	Q _{RR}	_	2.3	_	μC		

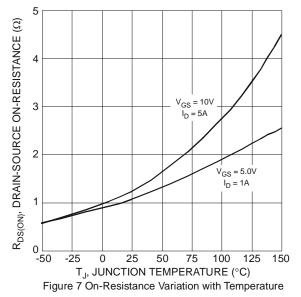
5. Device mounted on infinite heatsink.

- 6. Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
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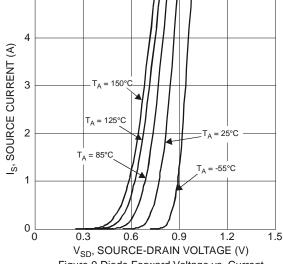


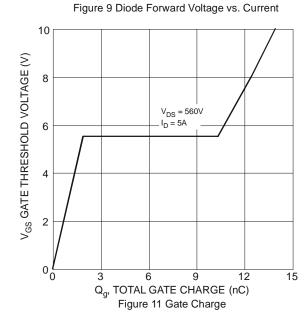












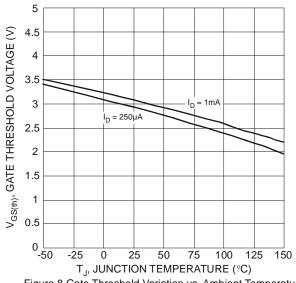
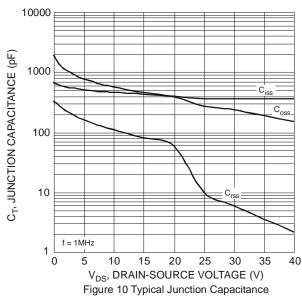
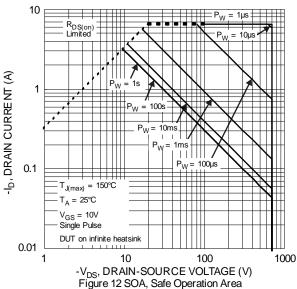
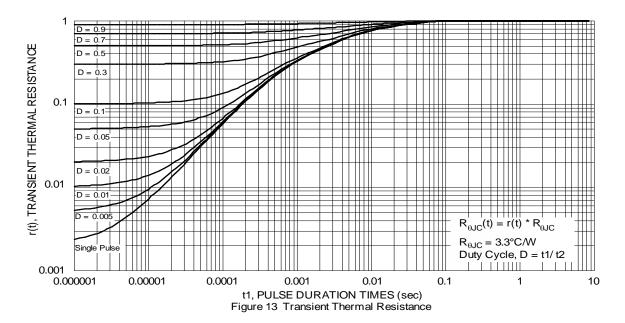


Figure 8 Gate Threshold Variation vs. Ambient Temperature







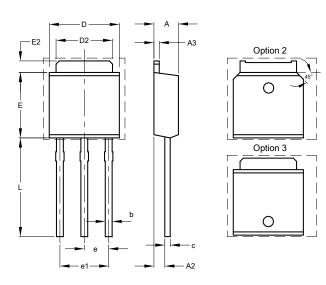




Package Outline Dimensions

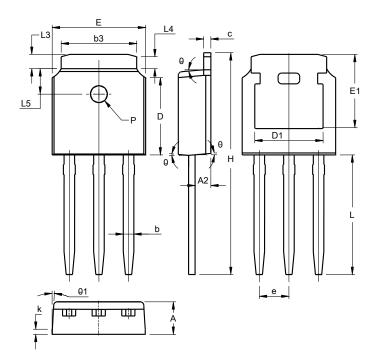
Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.

TO251



TO251					
Dim	Min	Max			
Α	2.200	2.400			
A2	0.890	1.150			
А3	0.450	0.550			
В	0.550	0.740			
C	0.450	0.570			
D	6.400	6.750			
D2	5.200	5.400			
Е	5.950	6.250			
E2	0.900	1.250			
Е	2.240	2.340			
e1	4.430	4.730			
L	8.900	9.500			
All Dimensions in mm					

TO251 (Type TH)



TO251 (Type TH)						
Dim	Min	Max	Тур			
Α	2.20	2.40	2.30			
A2	0.97	1.17	1.07			
b	0.68	0.90	0.78			
b3	5.20	5.50	5.33			
С	0.43	0.63	0.53			
D	5.98	6.22	6.10			
D1	5	5.30 REF	=			
е	2	.286 BS	С			
Ε	6.40	6.80	6.60			
E1	4.63	5.03	4.83			
Н	16.22	16.82	16.52			
k		0.40REF				
L	9.15	9.65	9.40			
L3	0.88	1.28	1.02			
L4	0.75 REF					
L5	1.65	1.95	1.80			
ΡØ	1.20					
θ	5°	9°	7°			
θ1	5°	9°	7°			
All Dimensions in mm						



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